



## 10N65-Q

Power MOSFET

### 10A, 650V N-CHANNEL POWER MOSFET

#### DESCRIPTION

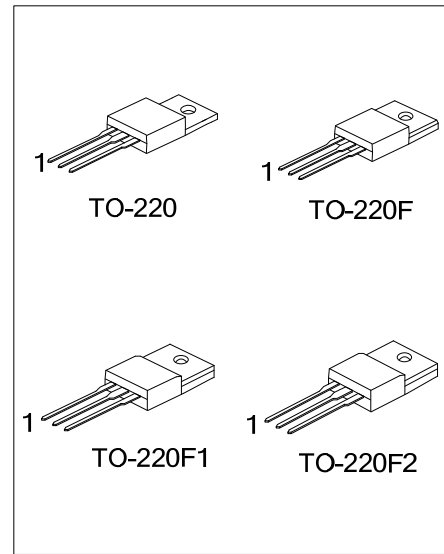
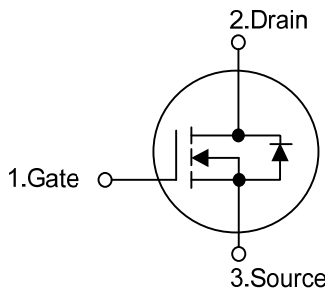
The UTC **10N65-Q** is an N-channel Power MOSFET using UTC's advanced technology to provide customers a minimum on-state resistance and superior switching performance, etc.

The UTC **10N65-Q** is generally applied in high efficient DC to DC converters, PWM motor controls and bridge circuits, etc.

#### FEATURES

- \*  $R_{DS(ON)} < 1.0\Omega$  @  $V_{GS}=10V, I_D = 5 A$
- \* High Switching Speed
- \* Improved dv/dt capability

#### SYMBOL



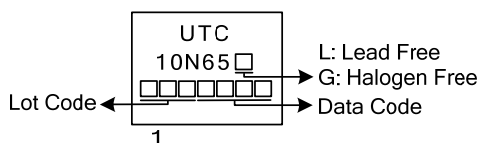
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N65L-TA3-T	10N65G-TA3-T	TO-220	G	D	S	Tube
10N65L-TF3-T	10N65G-TF3-T	TO-220F	G	D	S	Tube
10N65L-TF1-T	10N65G-TF1-T	TO-220F1	G	D	S	Tube
10N65L-TF2-T	10N65G-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

	<p>(1) T: Tube</p> <p>(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1 TF2: TO-220F2</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	650	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Avalanche Current (Note 2)		$I_{AR}$	10	A
Drain Current	Continuous	$I_D$	10	A
	Pulsed (Note 2)	$I_{DM}$	38	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	350	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220	$P_D$	156	W
	TO-220F/TO-220F1		50	W
	TO-220F2		48	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Operating Temperature		$T_{OPR}$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L=7\text{mH}$ ,  $I_{AS}=10\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 10\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	$\theta_{JC}$	0.8	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.5	$^\circ\text{C}/\text{W}$
	TO-220F2		2.6	$^\circ\text{C}/\text{W}$

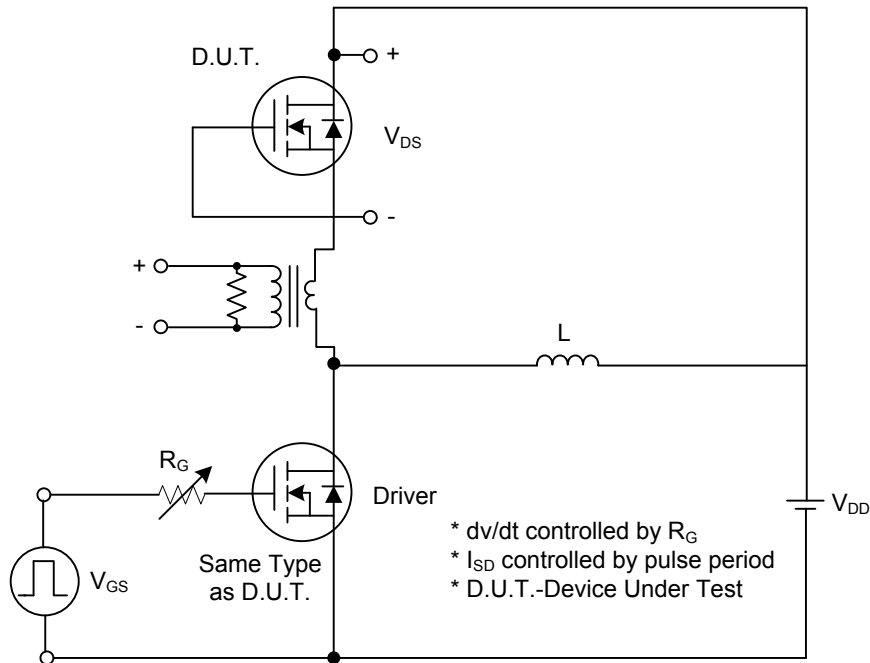
■ ELECTRICAL CHARACTERISTICS(  $T_C=25^{\circ}\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V$			1	$\mu A$
Gate-Source Leakage Current	Forward	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
	Reverse		$V_{GS} = -30V, V_{DS} = 0V$			-100
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 5A$			1.0	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=25V, V_{GS}=0V, f=1.0\text{ MHz}$		1500		pF
Output Capacitance	$C_{OSS}$			130		pF
Reverse Transfer Capacitance	$C_{RSS}$			25		pF
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=30V, I_D=0.5A,$ $R_G=25\Omega$ (Note 1, 2)		60		ns
Turn-On Rise Time	$t_R$			120		ns
Turn-Off Delay Time	$t_{D(OFF)}$			310		ns
Turn-Off Fall Time	$t_F$			180		ns
Total Gate Charge	$Q_G$	$V_{DS}=50V, I_D=1.3A,$ $V_{GS}=10V$ (Note 1, 2)		39		nC
Gate-Source Charge	$Q_{GS}$			8.0		nC
Gate-Drain Charge	$Q_{GD}$			9.5		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 10A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	$I_S$				10	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$				40	A
Reverse Recovery Time	$t_{RR}$	$V_{GS}=0V, I_S=10A$ $di_F/dt = 100\text{ A}/\mu\text{s}$ (Note 1)		420		ns
Reverse Recovery Charge	$Q_{RR}$			4.2		$\mu\text{C}$

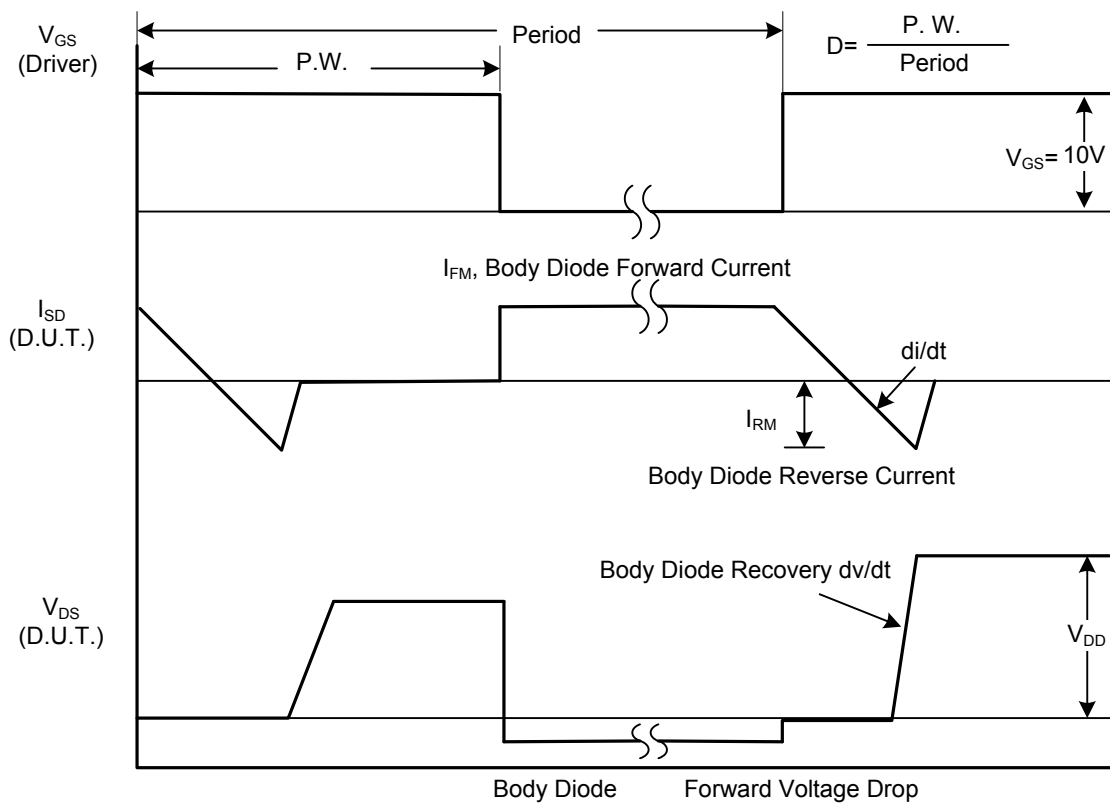
Note: 1. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

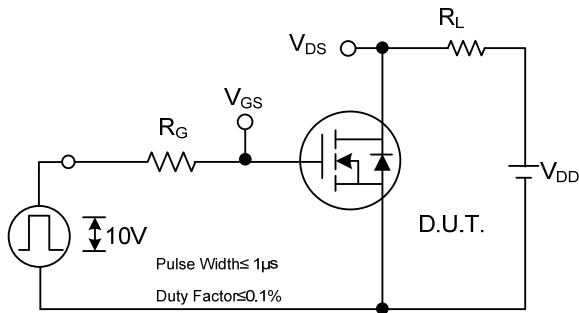


Peak Diode Recovery  $dv/dt$  Test Circuit

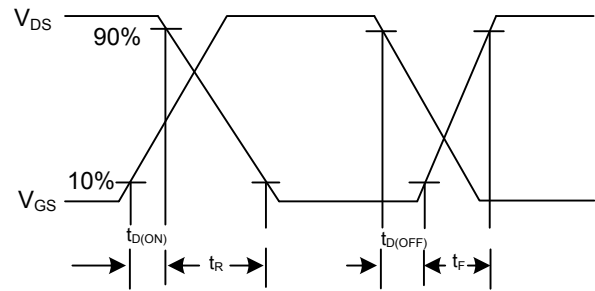


Peak Diode Recovery  $dv/dt$  Waveforms

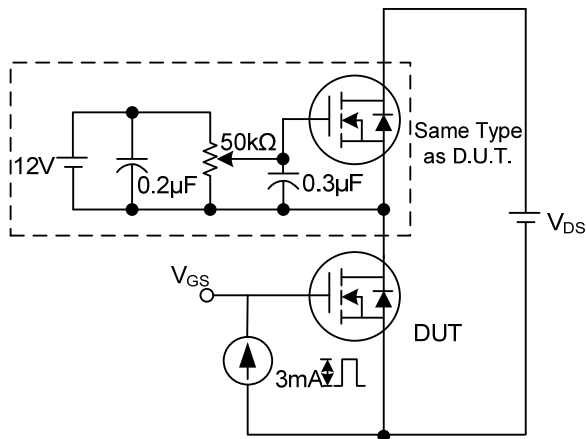
## TEST CIRCUITS AND WAVEFORMS (Cont.)



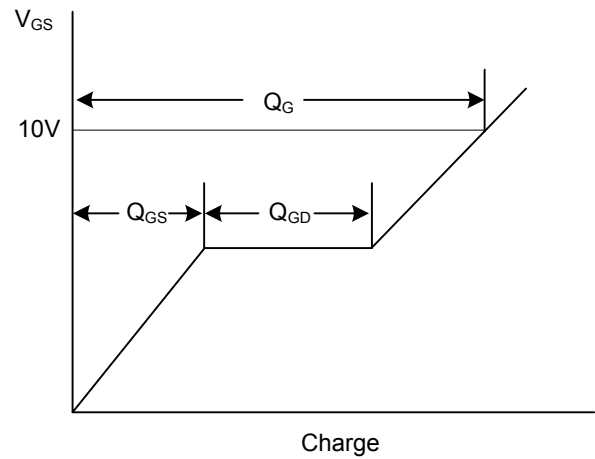
**Switching Test Circuit**



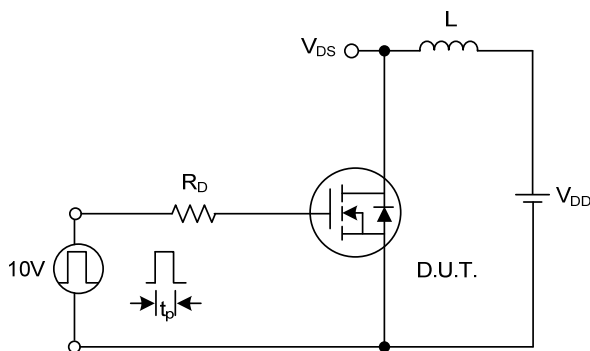
**Switching Waveforms**



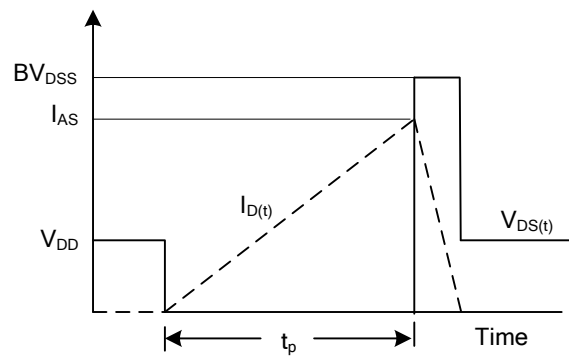
**Gate Charge Test Circuit**



**Gate Charge Waveform**



**Unclamped Inductive Switching Test Circuit**



**Unclamped Inductive Switching Waveforms**

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